

<b>INFORMATION</b>	Atty. Docket No. <b>960045D</b>	Serial No. <b>To be assigned</b>
	Applicant(s): <b>Taiji EMA et al.</b>	
	<b>CITATION</b>	Filing Date: <b>Herewith</b>

PTO-1449

### U.S. PATENT DOCUMENTS

Examiner Initial	Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
<u>an</u>	AB	5,502,336	Park et al.	03/96		
<u>an</u>	AC	5,479,054	Tottori	12/95		
<u>an</u>	AD	5,338,700	Dennison et al.	08/94		
<u>an</u>	AE	4,974,040	Taguchi et al.	11/90		
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<u>an</u>	AI	5,324,681	Lowrey et al.	06/94		
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<u>an</u>	AK	5,281,549	Fazan et al.	01/94		
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Document No.	Date	Country	Translation (Yes or No)
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<u>cn</u>	AV	I. NAIKI et al.; "Center Wordline Cell: A New Symmetric Layout Cell for 64Mb SRAM"; Technical Digest of IEDM; pages 817-820; December 1993.
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<u>cn</u>	AZ	Y. NISHIOKA et al.; "Giga-bit Scale DRAM Cell with New Simple Ru/(Ba,Sr)TiO <sub>3</sub> /Ru Stacked Capacitors Using X-ray Lithography"; Technical Digest of IEDM; pages 903-906; December 1995.
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<div> <div>Examiner</div> <div><i>QgG</i></div> <div>Date Considered</div> <div><i>10-28-04</i></div> </div>		